

P-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (m Ω)(Typ.)	I_D (A) ^a	Q_g (Typ.)
- 100	82 at $V_{GS} = - 10$ V	- 15	46 nC

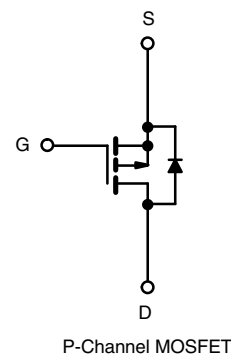
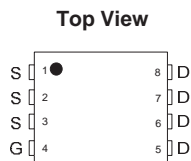
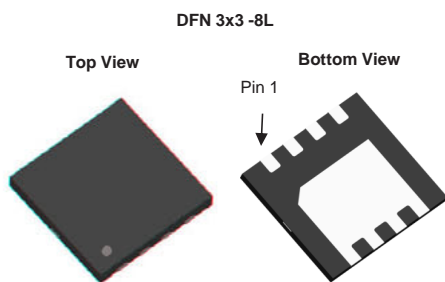
FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested
- Low Thermal Resistance



APPLICATIONS

- Active Clamp in IntermediateDC/DC Power Supplies



ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	- 100	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D	$T_C = 25$ °C	- 15
		$T_C = 100$ °C	- 9.4
Pulsed Drain Current ^b	I_{DM}	- 40	A
Single Avalanche Energy	E_{AS}	15	mJ
Maximum Power Dissipation ^c	P_D	$T_C = 25$ °C	60
		$T_C = 100$ °C	24
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to +150	°C

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient (PCB Mount) ^d	R_{thJA}	31	°C/W
Junction-to-Case (Drain)	R_{thJC}	2.08	

Notes

- Calculated continuous current based on maximum allowable junction temperature.
- Repetitive rating; pulse width limited by max. junction temperature.
- P_d is based on max. junction temperature, using junction-case thermal resistance.
- The value of R_{thJA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_a = 25$ °C.

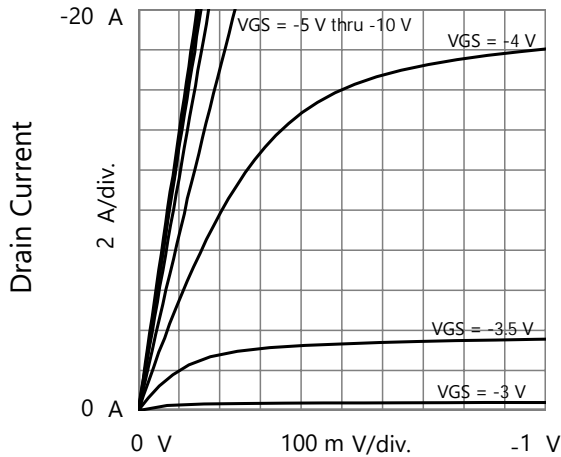
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0, I_D = -250\text{ }\mu\text{A}$	- 100			V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	- 2		- 4	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -100\text{ V}, V_{GS} = 0\text{ V}$			- 1	μA
		$V_{DS} = -80\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			- 10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq -5\text{ V}, V_{GS} = -10\text{ V}$	- 15			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -4\text{ A}$		82	105	$\text{m}\Omega$
Forward Transconductance ^a	g_{fs}	$V_{DS} = -5\text{ V}, I_D = -4\text{ A}$		23		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = -50\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		2050		pF
Output Capacitance	C_{oss}			148		
Reverse Transfer Capacitance	C_{rss}			125		
Total Gate Charge	Q_g	$V_{DS} = -50\text{ V}, V_{GS} = -10\text{ V}, I_D = -4\text{ A}$		46		nC
Gate-Source Charge	Q_{gs}			6		
Gate-Drain Charge	Q_{gd}			10		
Gate Resistance	R_g	$f = 1\text{ MHz}$		4.8		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -50\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong -4\text{ A}, V_{GEN} = -10\text{ V}, R_g = 3\text{ }\Omega$		14		ns
Rise Time	t_r			15		
Turn-Off Delay Time	$t_{d(off)}$			45		
Fall Time	t_f			13		
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			- 15	A
Pulse Diode Forward Current	I_{SM}				- 40	
Body Diode Voltage	V_{SD}	$I_S = -1\text{ A}$			- 1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -4\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		48		ns
Body Diode Reverse Recovery Charge	Q_{rr}			100		nC

Notes:

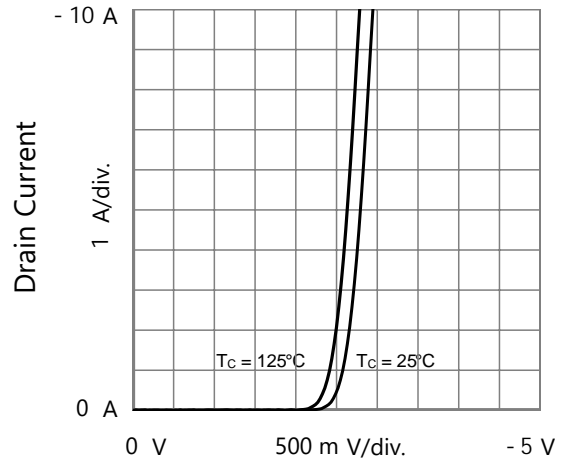
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

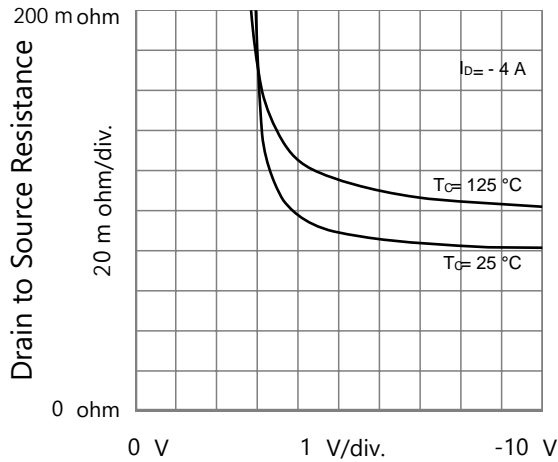
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



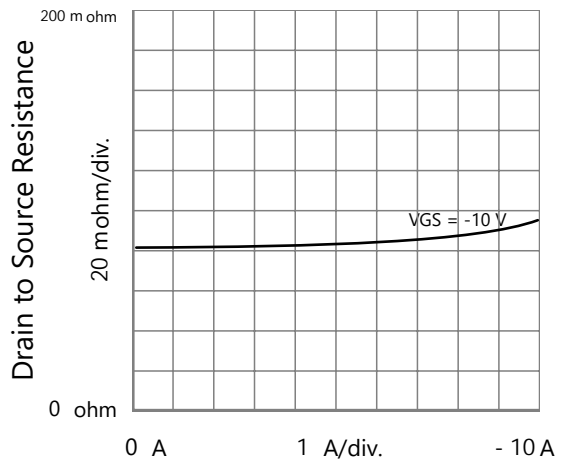
Drain to Source Voltage
Output Characteristics



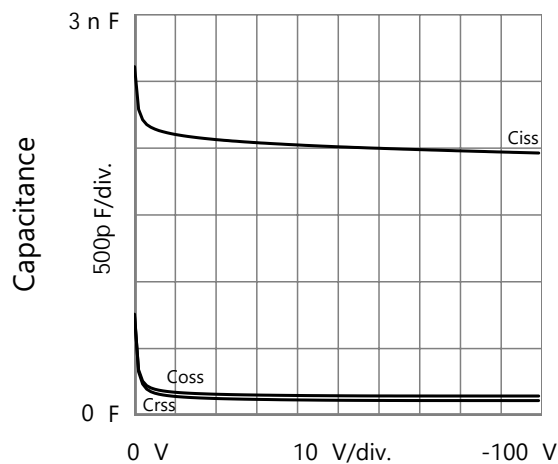
Gate to Source Voltage
Transfer Characteristics



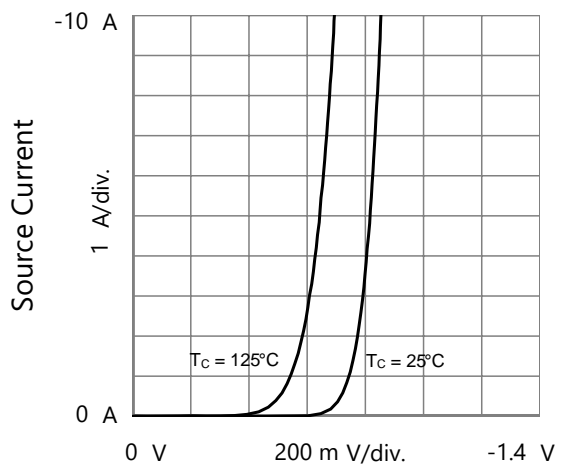
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



Drain Current
Drain to Source Resistance vs. Drain Current

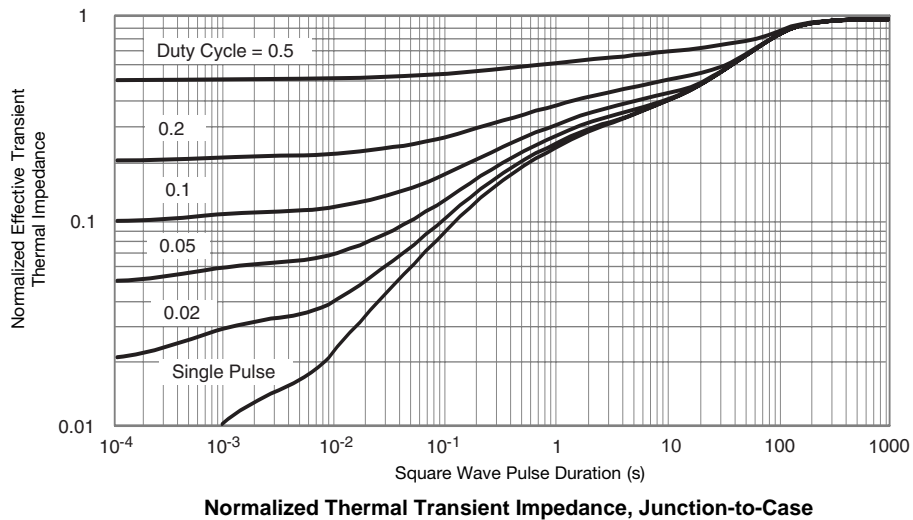
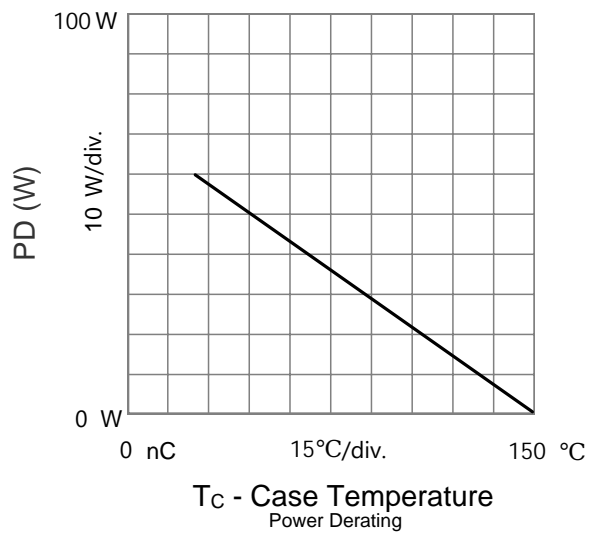
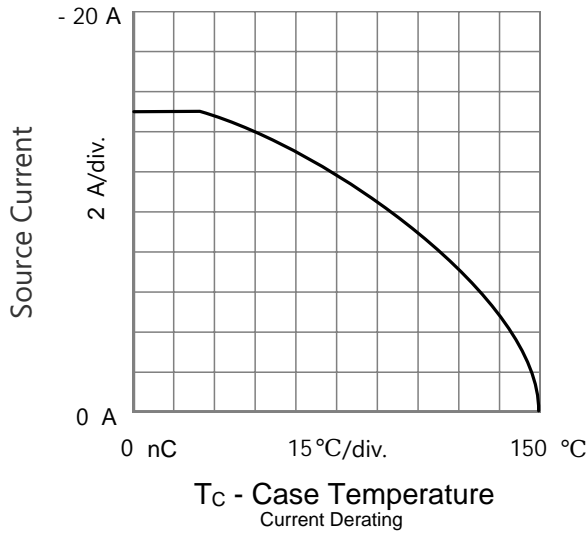
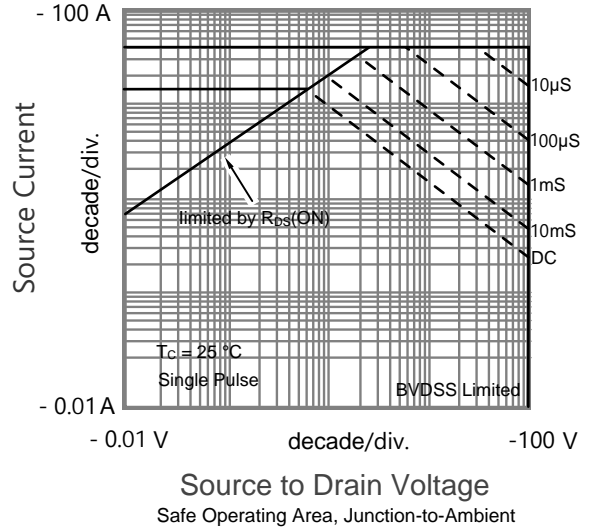
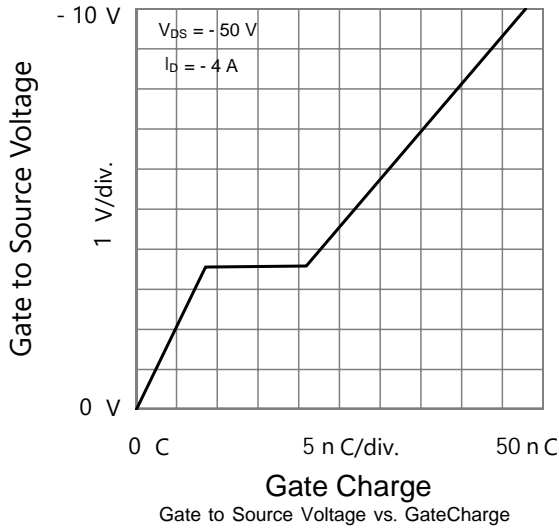


Drain to Source Voltage
Capacitances

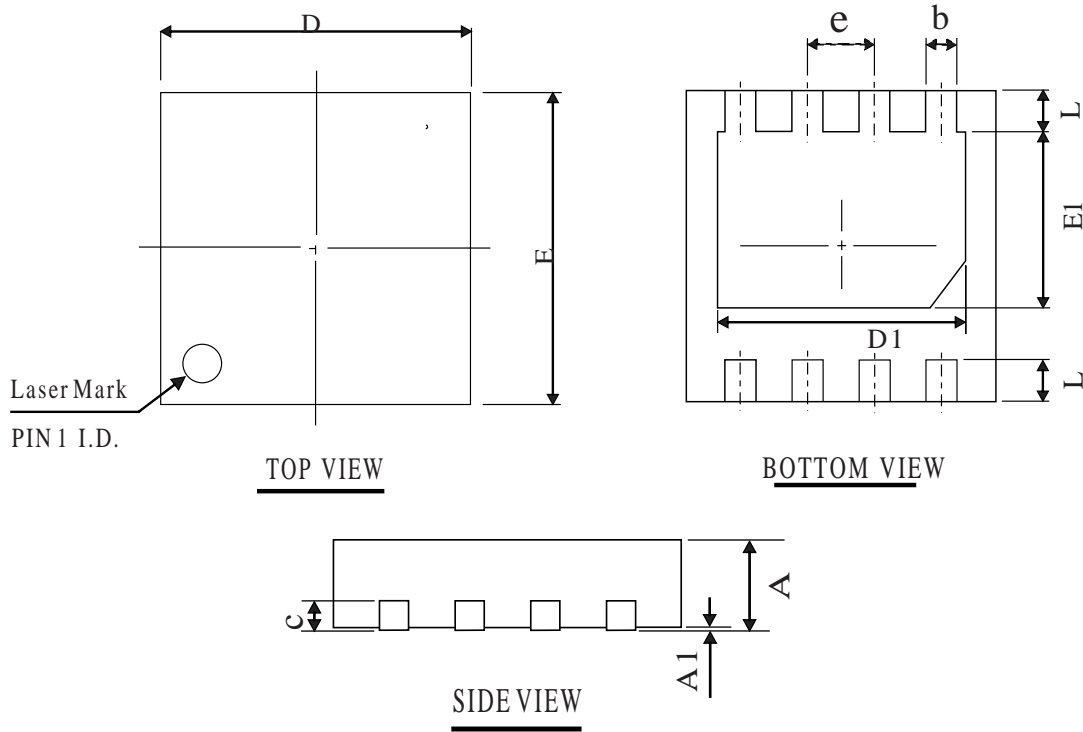


Source to Drain Voltage
Body Diode Forward Characteristics

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



DFN3*3-8L PACKAGE OUTLINE



COMMON DIMENSIONS
(UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	0.60	0.75	0.90
A1	0.00	0.02	0.08
b	0.20	0.30	0.45
D	2.85	3.00	3.15
E	2.85	3.00	3.15
D1	2.10	2.40	2.70
E1	1.50	1.70	2.00
L	0.20	0.40	0.60
C	0.203 REF		
e	0.65 BSC		

OTHER DIMENSIONS

A	0.50	0.55	0.60
A	0.40	0.45	0.50

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